



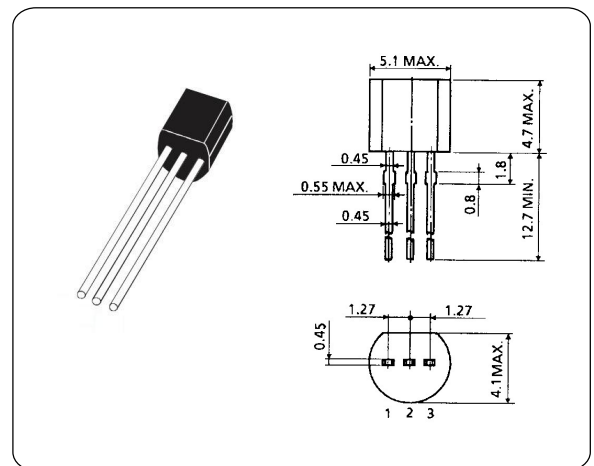
Silicon Bidirectional Triode Thyristors

STN1A60/80

GENERAL DESCRIPTION

Designed for use in solid state relays, MPU interface, TTL logic and any other light industrial or consumer application. Supplied in an inexpensive TO - 92 package which is readily adaptable for use in automatic insertion equipment.

Parameter	Symbol	Typ		Unit
		STN1A60	STN1A80	
Repetitive peak off-state voltages	V_{DRM} V_{RRM}	600	800	V
RMS on-state current	$I_{T(RMS)}$	1.0		A
Non-repetitive peak on-state current	I_{TSM}	10		A
Max. Operating Junction Temperature	T_j	110		°C
Storage Temperature	T_{stg}	-45~150		°C



Parameter		Symbol	Test Conditions	Min	Typ		Max	Unit
					STN1A60	STN1A80		
Repetitive peak off-state voltages		V_{DRM} V_{RRM}		—	600	800	—	V
RMS on-state current		$I_{T(RMS)}$	all conduction angles	—	1.0		—	A
On-state voltage		V_T	$I_T=1.5\text{ A}$	—	—		1.60	V
Holding current		I_H	$V_D=12\text{ V}; I_{GT}=10\text{ mA}$	—	—		5	mA
Gate trigger current	T2+G+	I_{GT}	$V_D=6.0\text{ V}; R_L=10\ \Omega$	—	—		5.0	mA
	T2+G-			—	—		5.0	
	T2-G-			—	—		5.0	
	T2-G+			—	—		12	
Gate trigger voltage		V_{GT}	$V_D=6.0\text{ V}; R_L=10\ \Omega$	—	0.5		1.8	V